HITACHI

ADE-208-421(Z)

HSC276
Silicon Schottky Barrier Diode for Tuner Mixer, converter

HITACHI

Rev. 0
Nov. 1995

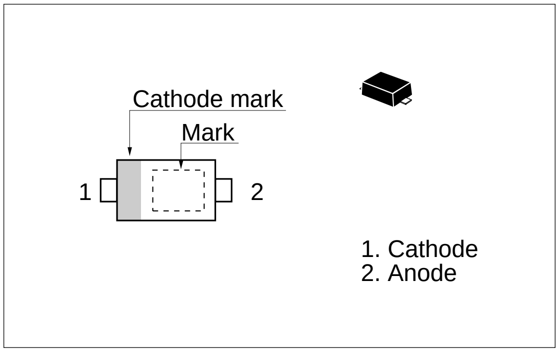
Features

- High forward current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HSC276	C2	UFP

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	3	V
Average forward current	I_o	30	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	I_R = 1 mA
Reverse current	I_R	—	—	50	µA	V_R= 0.5 V
Forward current	I_F	35	—	—	mA	V_F= 0.5 V
Capacitance	C	—	—	0.85	pF	V_R = 0.5 V, f = 1 MHz
ESD-Capability	—	30	—	—	V	*C=200pF , Both forward and reverse direction 1 pulse.

* Failure criterion ; $I_R \geq 100\mu A$ at V_R =0.5 V

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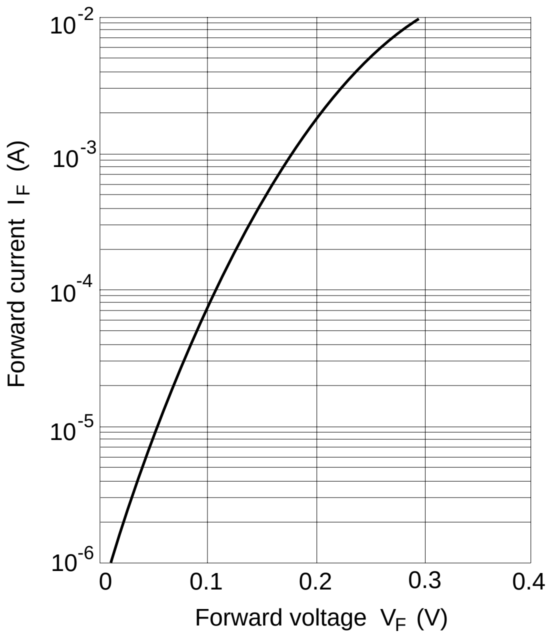


Fig.1 Forward current Vs. Forward voltage

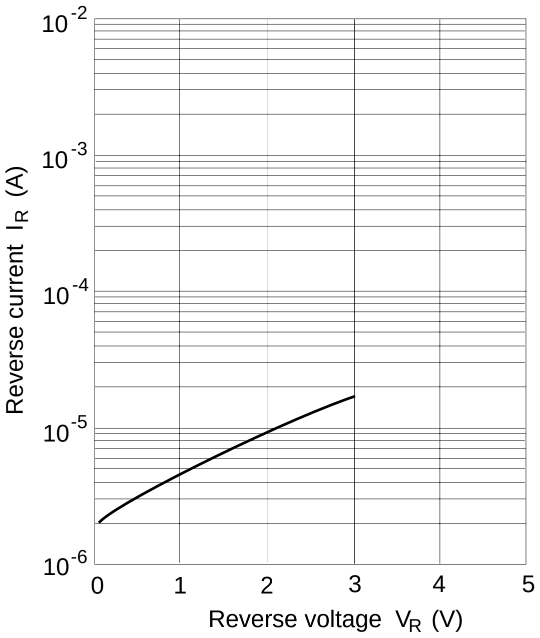


Fig.2 Reverse current Vs. Reverse voltage

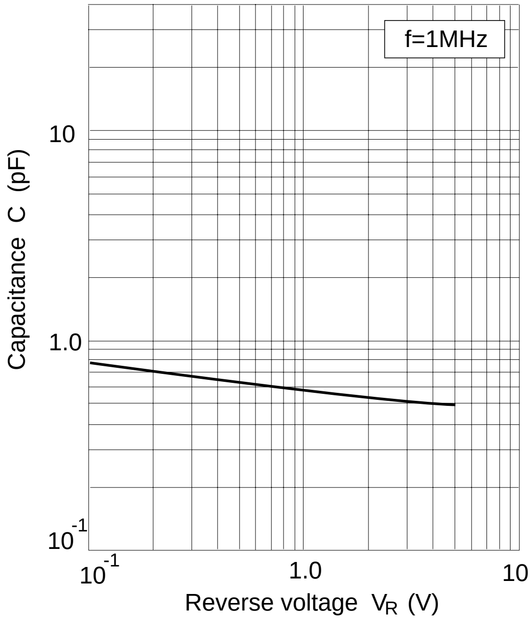
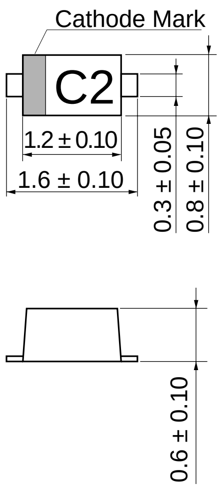


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Cathode
2 Anode

HITACHI Code	UFP
JEDEC Code	—
EIAJ Code	SC-79
Weight (g)	0.0016